ΡΛΝ	JIT
	SEMI
	CONDUCTOR

TO-252AA

Gate ^①

Drain

Source

PJD9P06A-AU

60V P-Channel Enhancement Mode MOSFET

Voltage

-60 V Current

Features

- R_{DS(ON)}, V_{GS}@-10V,I_D@-3.5A<170mΩ
- $R_{DS(ON)}$, V_{GS} @-4.5V, I_D @-2A<220m Ω
- High switching speed
- Improved dv/dt capability
- Low Gate Charge
- Low reverse transfer capacitance
- AEC-Q101 qualified
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 Standard

Mechanical Data

- Case : TO-252AA Package
- Terminals : Solderable per MIL-STD-750, Method 2026
- Approx. Weight : 0.0104 ounces, 0.297grams

Maximum Ratings and Thermal Characteristics (T_A=25°C unless otherwise noted)

-7 A

PARAMETE	R	SYMBOL	LIMIT	UNITS	
Drain-Source Voltage		V _{DS}	-60	V	
Gate-Source Voltage		V_{GS}	<u>+</u> 20	V	
Continuous Drain Current	T _C =25°C	I _D	-7.0	А	
	T _c =100°C		-4.3		
Pulsed Drain Current (Note 1)	T _c =25°C	I _{DM}	-28		
Power Dissipation	T _c =25°C	PD	15.6	W	
	$T_c=100^{\circ}C$		6.2		
Continuous Drain Current	T _A =25°C	I _D	-2.5	А	
	T _A =70°C		-2.0	А	
Power Dissipation	T _A =25°C	_	2.0		
Power Dissipation	T _A =70°C	PD	1.3	W	
Single Pulse Avalanche Energy (Note 6)		E _{AS}	32	mJ	
Operating Junction and Storage Temperature Range		T _J ,T _{STG}	-55~150	°C	
Typical Thermal resistance ^(Note 4,5)	Junction to Case	$R_{ extsf{ heta}JC}$	8	°C/W	
	Junction to Ambient	$R_{ extsf{ heta}JA}$	62.5		

• Limited only By Maximum Junction Temperature



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Electrical Characteristics ($T_A=25^{\circ}C$ unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	BV_{DSS}	V _{GS} =0V,I _D =-250uA	-60	-	-	
Gate Threshold Voltage	V _{GS(th)}	$V_{DS}=V_{GS}$, $I_{D}=-250$ uA	-1.0	-1.88	-2.5	V
Drain-Source On-State Resistance		V _{GS} =-10V,I _D =-3.5A	-	150	170	mΩ
	$R_{DS(on)}$	V _{GS} =-4.5V,I _D =-2A	-	190	220	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-60V,V _{GS} =0V	-	-	-1.0	uA
Gate-Source Leakage Current	I _{GSS}	V _{GS} = <u>+</u> 20V,V _{DS} =0V	-	-	<u>+</u> 100	nA
Dynamic (Note 7)		•				
Total Gate Charge	Qg	V _{DS} =-30V, I _D =-3A, V _{GS} =-10V ^(Note 2,3)	-	8.3	-	nC
Gate-Source Charge	Q _{gs}		-	1.8	-	
Gate-Drain Charge	Q _{gd}		-	1.6	-	
Input Capacitance	Ciss	V _{DS} =-30V, V _{GS} =0V, f=1.0MHZ	-	430	-	pF
Output Capacitance	Coss		-	33	-	
Reverse Transfer Capacitance	Crss		-	29	-	
Turn-On Delay Time	td _(on)	V _{DS} =-30V, I _D =-1.0A, V _{GS} =-10V, R _G =6Ω (Note 2.3)	-	5.1	-	
Turn-On Rise Time	tr		-	20	-	
Turn-Off Delay Time	td _(off)		-	36	-	ns
Turn-Off Fall Time	t _f	(-	11	-	
Drain-Source Diode						
Maximum Continuous Drain-Source					7	А
Diode Forward Current	I _S		-	-	-7	
Reverse Recovery Time	V _{SD}	I _S =-1A,V _{GS} =0V	-	-0.76	-1.0	V

NOTES :

- 1. Pulse width</br>
- 2. Essentially independent of operating temperature typical characteristics
- 3. Repetitive rating, pulse width limited by junction temperature TJ(MAX)=150°C. Ratings are based on low frequency and duty cycles to keep initial TJ =25°C.
- 4. The maximum current rating is package limited
- 5. $R_{\Theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch² with 2oz.square pad of copper
- 6. L=1mH, I_{AS} =-8A, V_{GS} =-10V, V_{DS} =-25V, R_{G} =25 ohm
- 7. Guaranteed by design, not subject to production testing.

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6

175

PJD9P06A-AU **TYPICAL CHARACTERISTIC CURVES** 10 10 V_{GS}‡-10V,-8V V_{DS}=-5V -I_{DS}-Drain-to-S ource Current(A) -I_{DS}-Drain-to-S ource Current(A) 8 8 V_{GS}=-4V 6 6 4 4 T_J=125°C T_=25℃ V_{GS}=-3V 2 2 0 0 0 2 3 5 0 2 3 5 -V_{DS}- Drain-to-Source Voltage(V) -V_{GS}-Gate-to-Source Voltage(V) **Fig.1 On-Region Characteristics Fig.2 Transfer Characteristics** 300 2.0 R_{Ds}(on)- On-Resistance (Normalized) $R_{DS}(on)$ - On-Resistance(m Ω) 250 1.7 V_{GS}=-10V, I_D=-3.5A V_{GS}=-4.5V 1.4 200 V_{GS}=-4.5V, I_D=-2A V_{GS}=-10V 1.1 150 0.8 100 100 0 25 50 75 125 150 0 2 4 6 8 10 Temperature (°C) -I_{DS}-Drain-to-Source Current(A) Fig.3 On-Resistance vs. Drain Current Fig.4 On-Resistance vs. Junction temperature 10 500 I_D=-1.75A R_{Ds}(on)- On-Resistance(mΩ) 400 1 300 T_i=125℃ 0.1 T_i=25°C 200

-I_{sD}-Source-to-Drain Current(A) T_j=125℃ T_i=25°C 0.01 100 2 10 0 0.3 0.6 0.9 1.2 4 6 8 -V_{GS}-Gate-to-Source Voltage(V) -V_{SD}-Source-to-Drain Voltage(V) Fig.5 On-Resistance Variation with VGS. **Fig.6 Body Diode Characteristics**

June 20,2019-REV.00

-V_{TH}-Gate-to-Source Voltage(V) 6 4 2 0 0 2 6 8 10 4 Qg(nC)

Fig.7 Gate-Charge Characteristics

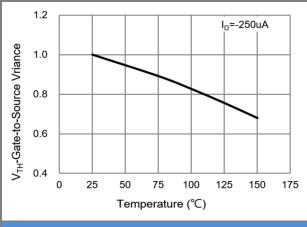
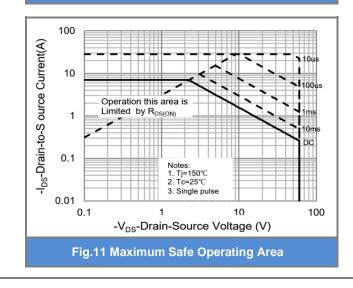
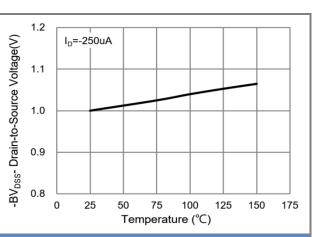


Fig.9 Threshold Voltage Variation with Temperature.







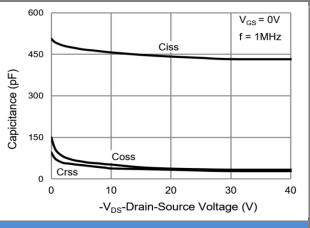


Fig.10 Capacitance vs. Drain-Source Voltage.

Page 4





10

8

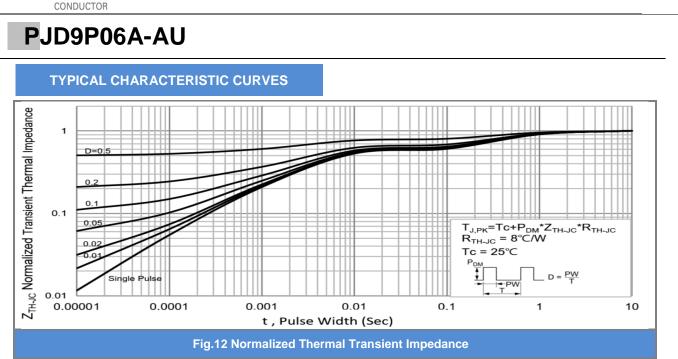
TYPICAL CHARACTERISTIC CURVES

PJD9P06A-AU

V_{DS}=-30V I_D=-3A







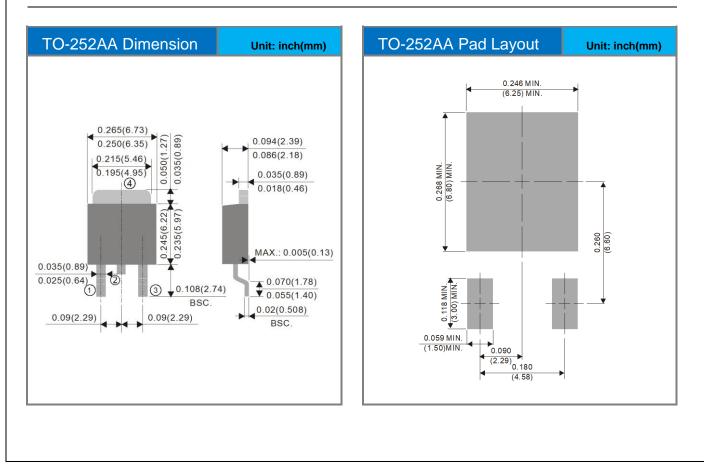


PJD9P06A-AU

Part No Packing Code Version

Part No Packing Code	Package Type	Packing Type Marking		Version
PJD9P06A-AU_L2_000A1	TO-252AA	3,000pcs / 13" reel	D9P06A	Halogen free

Packaging Information & Mounting Pad Layout





PJD9P06A-AU

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